



HM-6504

T-46-23-05

4096 x 1 CMOS RAM

February 1992

Features

- **Low Power Standby** 125 μ W Max.
- **Low Power Operation** 35mW/MHz Max.
- **Data Retention** @2.0V Min.
- **TTL Compatible Input/Output**
- **Three-State Output**
- **Standard JEDEC Pinout**
- **Fast Access Time** 120/200ns Max.
- **18 Pin Package for High Density**
- **On-Chip Address Register**
- **Gated Inputs - No Pull Up or Pull Down Resistors Required**

Description

The HM-6504 is a 4096 x 1 static CMOS RAM fabricated using self-aligned silicon gate technology. The device utilizes synchronous circuitry to achieve high performance and low power operation.

On chip latches are provided for addresses, data input and data output allowing efficient interfacing with microprocessor systems. The data output can be forced to a high impedance state for use in expanded memory arrays.

Gated inputs allow lower operating current and also eliminate the need for pull up or pull down resistors. The HM-6504 is a fully static RAM and may be maintained in any state for an indefinite period of time.

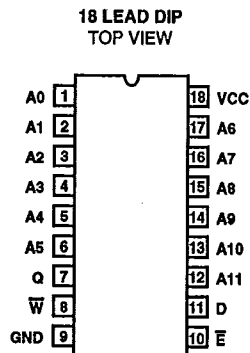
Data retention supply voltage and supply current are guaranteed over temperature.

Ordering Information

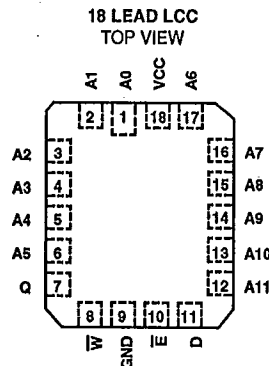
| PACKAGE | TEMPERATURE RANGE | 120ns | 200ns | 300ns |
|---|-------------------|---------------|---------------|--------------|
| Plastic DIP | -40°C to +85°C | HM3-6504S-9 | HM3-6504B-9 | HM3-6504-9 |
| Ceramic DIP * /883 JAN # SMD # | -40°C to +85°C | HM1-6504S-9 | HM1-6504B-9 | HM1-6504-9 |
| | -55°C to +125°C | HM1-6504S/883 | HM1-6504B/883 | HM1-6504/883 |
| | | 24501BVA | - | - |
| | | 810240IVA | 8102403VA | 8102405VA |
| LCC | -40°C to +85°C | - | HM4-6504B-9 | HM4-6504-9 |
| | -55°C to +125°C | - | HM4-6504B-8 | HM4-6504-8 |

*Respective /883 specifications are included at the end of this data sheet.

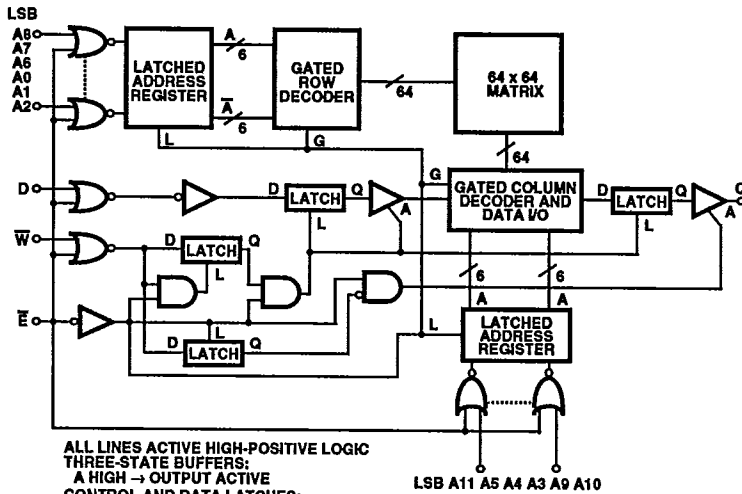
Pinouts



| PIN | DESCRIPTION |
|-----------|---------------|
| A | Address Input |
| \bar{E} | Chip Enable |
| \bar{W} | Write Enable |
| D | Data Input |
| Q | Data Output |



Functional Diagram



ALL LINES ACTIVE HIGH-POSITIVE LOGIC
 THREE-STATE BUFFERS:
 A HIGH → OUTPUT ACTIVE
 CONTROL AND DATA LATCHES:
 L LOW → Q = D
 Q LATCHES ON RISING EDGE OF L
 ADDRESS LATCHES:
 LATCH ON FALLING EDGE OF \bar{E}
 GATED DECODERS:
 GATE ON RISING EDGE OF G

Specifications HM-6504-9

T-46-23-05

Absolute Maximum Ratings

| | |
|--|----------------------|
| Supply Voltage | +7.0V |
| Input, Output or I/O Voltage | GND-0.3V to VCC+0.3V |
| Storage Temperature Range | -65°C to +150°C |
| Junction Temperature | +175°C |
| Lead Temperature (Soldering 10s) | +300°C |
| ESD Classification | Class 1 |

Reliability Information

| | | |
|---|---------------|---------------|
| Thermal Resistance | θ_{ja} | θ_{jc} |
| Ceramic DIP Package | 66°C/W | 12°C/W |
| Maximum Package Power Dissipation at +125°C | | |
| Ceramic DIP Package | 0.75W | |
| Gate Count | 6910 Gates | |

CAUTION: Stresses above those listed in "Absolute Maximum Ratings" may cause permanent damage to the device. This is a stress only rating and operation of the device at these or any other conditions above those indicated in the operational sections of this specification is not implied.

Operating Conditions

| | | |
|-------------------------------|----------------|---|
| Operating Voltage Range | +4.5V to +5.5V | Operating Temperature Range |
| | | HM-6504S-9, HM-6504B-9, HM-6504-9 |
| | | HM-6504B-8, HM-6504-8 |
| | | -40°C to +85°C |
| | | -55°C to +125°C |

DC Electrical Specifications VCC = 5V ± 10%; T_A = -40°C to +85°C (HM-6504B-9, HM-6504-9)
T_A = -55°C to +125°C (HM-6504B-8, HM-6504-8)

| SYMBOL | PARAMETER | MIN | MAX | UNITS | TEST CONDITIONS | |
|--------|-----------------------------------|-----------|---------|-------|--|--|
| ICCSB | Standby Supply Current | HM-6504-9 | - | 25 | μA | IO = 0mA, \bar{E} = VCC - 0.3V, VCC = 5.5V |
| | | HM-6504-8 | - | 50 | μA | |
| ICCOP | Operating Supply Current (Note 1) | - | 7 | mA | \bar{E} = 1MHz, IO = 0mA, VI = GND, VCC = 5.5V | |
| ICCDR | Data Retention Supply Current | HM-6504-9 | - | 15 | μA | IO = 0mA, VCC = 2.0V, \bar{E} = VCC |
| | | HM-6504-8 | - | 25 | μA | |
| VCDDR | Data Retention Supply Voltage | 2.0 | - | V | | |
| II | Input Leakage Current | -1.0 | +1.0 | μA | VI = VCC or GND, VCC = 5.5V | |
| IOZ | Output Leakage Current | -1.0 | +1.0 | μA | VO = VCC or GND, VCC = 5.5V | |
| VIL | Input Low Voltage | -0.3 | 0.8 | V | VCC = 4.5V | |
| VIH | Input High Voltage | VCC-2.0 | VCC+0.3 | V | VCC = 5.5V | |
| VOL | Output Low Voltage | - | 0.4 | V | IO = 2.0mA, VCC = 4.5V | |
| VOH1 | Output High Voltage | 2.4 | - | V | IO = -1.0mA, VCC = 4.5V | |
| VOH2 | Output High Voltage (Note 2) | VCC - 0.4 | - | V | IO = -100μA, VCC = 4.5V | |

Capacitance T_A = +25°C

| SYMBOL | PARAMETER | MAX | UNITS | TEST CONDITIONS |
|--------|-----------------------------|-----|-------|---|
| CI | Input Capacitance (Note 2) | 8 | pF | f = 1MHz, All measurements are referenced to device GND |
| CO | Output Capacitance (Note 2) | 10 | pF | |

NOTES:

1. Typical derating 5mA/MHz increase in ICCOP.
2. Tested at initial design and after major design changes.

Specifications HM-6504

T-46-23-05

AC Electrical Specifications VCC = 5V ± 10%; T_A = -40°C to +85°C (HM-6504S-9, HM-6504B-9, HM-6504-9)
T_A = -55°C to +125°C (HM-6504B-8, HM-6504-8)

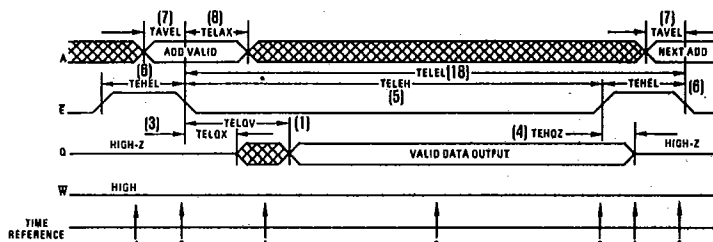
| SYMBOL | PARAMETER | HM-6504S | | HM-6504B | | HM-6504 | | UNITS | TEST CONDITIONS |
|------------|-----------------------------------|----------|-----|----------|-----|---------|-----|-------|-----------------|
| | | MIN | MAX | MIN | MAX | MIN | MAX | | |
| (1) TELQV | Chip Enable Access Time | - | 120 | - | 200 | - | 300 | ns | (Notes 1, 3) |
| (2) TAVQV | Address Access Time | - | 120 | - | 220 | - | 320 | ns | (Notes 1, 3, 4) |
| (3) TELQX | Chip Enable Output Enable Time | 5 | - | 5 | - | 5 | - | ns | (Notes 2, 3) |
| (4) TEHQZ | Chip Enable Output Disable Time | - | 50 | - | 80 | - | 100 | ns | (Notes 2, 3) |
| (5) TELEH | Chip Enable Pulse Negative Width | 120 | - | 200 | - | 300 | - | ns | (Notes 1, 3) |
| (6) TEHEL | Chip Enable Pulse Positive Width | 50 | - | 90 | - | 120 | - | ns | (Notes 1, 3) |
| (7) TAVEL | Address Setup Time | 0 | - | 20 | - | 20 | - | ns | (Notes 1, 3) |
| (8) TELAX | Address Hold Time | 40 | - | 50 | - | 50 | - | ns | (Notes 1, 3) |
| (9) TWLWH | Write Enable Pulse Width | 20 | - | 60 | - | 80 | - | ns | (Notes 1, 3) |
| (10) TWLEH | Write Enable Pulse Setup Time | 70 | - | 150 | - | 200 | - | ns | (Notes 1, 3) |
| (11) TWLEL | Early Write Pulse Setup Time | 0 | - | 0 | - | 0 | - | ns | (Notes 1, 3) |
| (12) TWHEL | Write Enable Read Mode Setup Time | 0 | - | 0 | - | 0 | - | ns | (Notes 1, 3) |
| (13) TELWH | Early Write Pulse Hold Time | 40 | - | 60 | - | 80 | - | ns | (Notes 1, 3) |
| (14) TDVWL | Data Setup Time | 0 | - | 0 | - | 0 | - | ns | (Notes 1, 3) |
| (15) TDVEL | Early Write Data Setup Time | 0 | - | 0 | - | 0 | - | ns | (Notes 1, 3) |
| (16) TWLDX | Data Hold Time | 25 | - | 60 | - | 80 | - | ns | (Notes 1, 3) |
| (17) TELDX | Early Write Data Hold Time | 25 | - | 60 | - | 80 | - | ns | (Notes 1, 3) |
| (18) TELEL | Read or Write Cycle Time | 170 | - | 290 | - | 420 | - | ns | (Notes 1, 3) |

NOTES:

- Input pulse levels: 0.8V to VCC - 2.0V; Input rise and fall times: 5ns (max); Input and output timing reference level: 1.5V; Output load: 1 TTL gate equivalent, CL = 50pF (min) - for CL greater than 50pF, access time is derated by 0.15ns per pF.
- Tested at initial design and after major design changes.
- VCC = 4.5V and 5.5V.
- TAVQV = TELQV + TAVEL.

Timing Waveforms

READ CYCLE



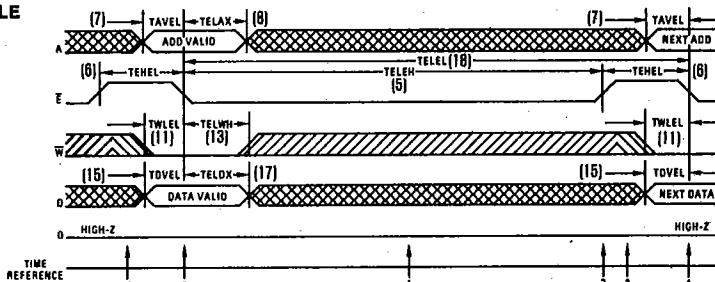
TRUTH TABLE

| TIME REFERENCE | INPUTS | | | OUTPUT | FUNCTION |
|----------------|-----------|-----------|---|--------|---|
| | \bar{E} | \bar{W} | A | Q | |
| -1 | H | X | X | Z | Memory Disabled |
| 0 | | H | V | Z | Cycle Begins, Addresses are Latched |
| 1 | L | H | X | X | Output Enabled |
| 2 | L | H | X | V | Output Valid |
| 3 | | H | X | V | Read Accomplished |
| 4 | H | X | X | Z | Prepare for Next Cycle (Same as -1) |
| 5 | | H | V | Z | Cycle Ends, Next Cycle Begins (Same as 0) |

The address information is latched in the on chip registers on the falling edge of \bar{E} (T = 0). Minimum address set up and hold time requirements must be met. After the required hold time, the addresses may change state without affecting the device operation. During time (T = 1) the output becomes

enabled but the data is not valid until during time (T = 2). \bar{W} must remain high for the read cycle. After the output data has been read, \bar{E} may return high (T = 3). This will disable the output buffer and all input and ready the RAM for the next memory cycle (T = 4).

EARLY WRITE CYCLE



TRUTH TABLE

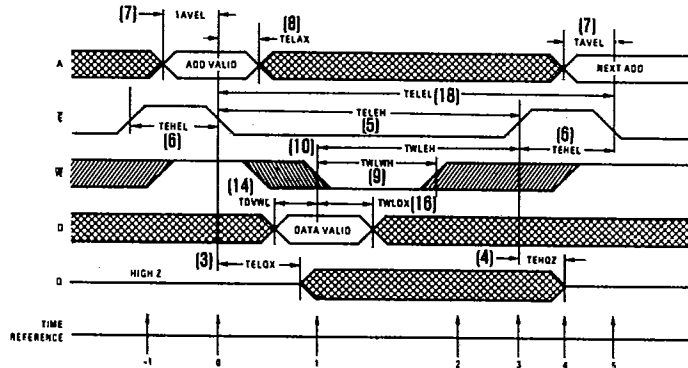
| TIME REFERENCE | INPUTS | | | | OUTPUT | FUNCTION |
|----------------|-----------|-----------|---|---|--------|---|
| | \bar{E} | \bar{W} | A | D | Q | |
| -1 | H | X | X | X | Z | Memory Disabled |
| 0 | | L | V | V | Z | Cycle Begins, Addresses are Latched |
| 1 | L | X | X | X | Z | Write in Progress Internally |
| 2 | | X | X | X | Z | Write Completed |
| 3 | H | X | X | X | Z | Prepare for Next Cycle (Same as -1) |
| 4 | | L | V | V | Z | Cycle Ends, Next Cycle Begins (Same as 0) |

The early write cycle is the only cycle where the output is guaranteed not to become active. On the falling edge of \bar{E} (T = 0), the addresses, the write signal, and the data input are latched in on chip registers. The logic value of \bar{W} at the time \bar{E} falls determines the state of the output buffer for that cycle. Since \bar{W} is low when \bar{E} falls, the output buffer is latched into the high impedance state and will remain in that

state until \bar{E} returns high (T = 2). For this cycle, the data input is latched by \bar{E} going low; therefore data set up and hold times should be referenced to \bar{E} . When \bar{E} (T = 2) returns to the high state the output buffer and all inputs are disabled and all signals are unlatched. The device is now ready for the next cycle.

Timing Waveforms (Continued)

LATE WRITE CYCLE



TRUTH TABLE

| TIME REFERENCE | INPUTS | | | | OUTPUTS | FUNCTION |
|----------------|--------|---|---|---|---------|---|
| | E | W | A | D | Q | |
| -1 | H | X | X | X | Z | Memory Disabled |
| 0 | L | H | V | X | Z | Cycle Begins, Addresses are Latched |
| 1 | L | L | X | V | X | Write Begins, Data is Latched |
| 2 | L | H | X | X | X | Write In Progress Internally |
| 3 | H | H | X | X | X | Write Completed |
| 4 | H | X | X | X | Z | Prepare for Next Cycle (Same as -1) |
| 5 | L | H | V | X | Z | Cycle Ends, Next Cycle Begins (Same as 0) |

The late write cycle is a cross between the early write cycle and the read-modify-write cycle.

Recall that in the early write the output is guaranteed to remain high impedance, and in the read-modify-write the output is guaranteed valid at access time. The late write is

between these two cases. With this cycle the output may become active, and may become valid data, or may remain active but undefined. Valid data is written into the RAM if data setup, data hold, write setup and write pulse widths are observed.

Test Load Circuit

